

Title (en)
Liquid crystal device

Title (de)
Flüssigkristallvorrichtung

Title (fr)
Dispositif à cristal liquide

Publication
EP 0789261 A1 19970813 (EN)

Application
EP 97102099 A 19970210

Priority
JP 2406496 A 19960209

Abstract (en)
A liquid crystal device is constituted by a pair of oppositely disposed substrates (11,12) each provided with an alignment control layer (15,16), and a liquid crystal layer (17) comprising a liquid crystal material and disposed between the substrates with a spacer member (18). In the device, the spacer member (18) has an electrical conductivity larger than that of the liquid crystal material. Further, the liquid crystal layer containing the spacer member has a first resistance in a direction of a normal to the substrates in a prescribed temperature range substantially lower than a second resistance of a corresponding liquid crystal layer, in the identical direction, consisting only of the liquid crystal material and having the identical plane area and thickness. The liquid crystal device is effective in providing an improved drive margin in a wide temperature range while suppressing a DC offset voltage component applied to the liquid crystal layer. <IMAGE>

IPC 1-7
G02F 1/1339; **G02F 1/1333**; **G02F 1/1337**; **G02F 1/141**

IPC 8 full level
G02F 1/133 (2006.01); **G02F 1/1333** (2006.01); **G02F 1/1339** (2006.01)

CPC (source: EP US)
G02F 1/133345 (2013.01 - EP US); **G02F 1/13392** (2013.01 - EP US)

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- [X] PATENT ABSTRACTS OF JAPAN vol. 018, no. 481 (P - 1797) 7 September 1994 (1994-09-07)
- [A] PATENT ABSTRACTS OF JAPAN vol. 018, no. 178 (P - 1717) 25 March 1994 (1994-03-25)

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